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ABSTRACT OF THE DISCLOSURE

Dot-pattern-like impurity regions are artificially and locally formed in a channel forming region. The impurity regions restrain the expansion of a drain side depletion layer toward the channel forming region to prevent the short channel effect. The impurity regions allow a channel width W to be substantially fined, and the resultant narrow channel effect releases the lowering of a threshold value voltage which is caused by the short channel effect.

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